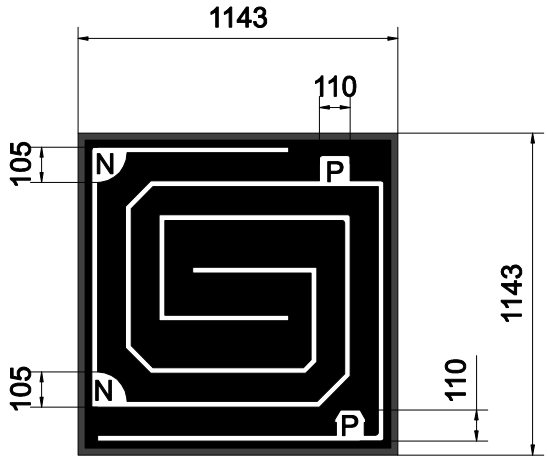
LED - Chip

ELC-525-31-2

26.05.2008 rev. 02

Radiation		Technology	Electrodes
Green		$InGaN/Al_2O_3$	Both on top side



typ. dimensions (µm)

typ. thickness
100 (±10) µm

p and n contact
gold alloy

backside metalization
gold alloy

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		2.8	3.2	V
Forward voltage[1]	I_F = 350 mA	V_F		3.6		V
Reverse voltage	I_R = 10 µA	V_R	5			V
Radiant power[1]	I_F = 350 mA	Φ_e	80	110		mW
Luminous intensity[1)]	I_F = 20 mA	I_V	750	850		mcd
Luminous intensity[1)]	I_F = 350 mA	I_V	7500	9000		mcd
Peak wavelength	I_F = 350 mA	λ_P	505	515	525	nm
Dominant wavelength	I_F = 350 mA	λ_D	515	525	535	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		35		nm
Switching time	I_F = 20 mA	t_r, t_f		50		ns

[1)]Measured on bare chip with *EPIGAP* equipment

Labeling

Type	Lot N°	I_v(typ) [mcd]	V_F(typ) [V]	Quantity
ELC-525-31-2				

Packing: Chips on adhesive film with wire-bond side on top

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